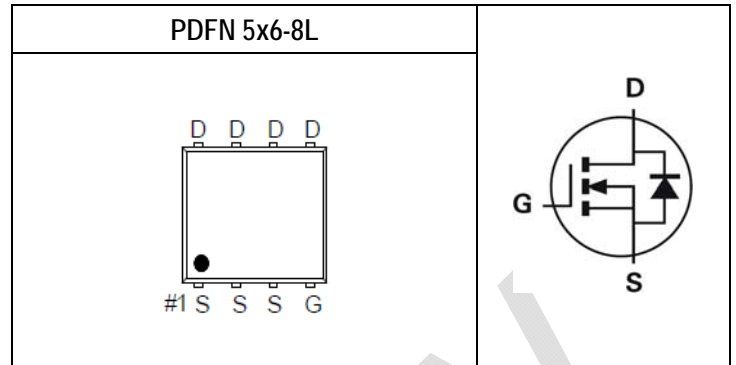


Key Performance Parameters		
Parameter	Value	Unit
V_{DSS}	30	V
$R_{DS(ON) \max.} V_{GS}=10V$	2.7	m Ω
I_D	70	A
Q_g	43.1	nC
Q_{gd}	9.57	nC
Q_{SW}	13.6	nC



Features	Application
<ul style="list-style-type: none"> Optimized for synchronous rectification Low Input Capacitance Low Miller Capacitance Fully Characterized Capacitance and Avalanche Pb-free lead plating; RoHS compliant 	<ul style="list-style-type: none"> BLDC Motor drive applications Battery powered circuits Synchronous rectifier applications Resonant mode power supplies

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
DG30N17Q	Halogen-Free	PDFN 5x6-8L	Q	Tape & Reel	2,500

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	$T_C=25^\circ\text{C}$	49
		$T_C=100^\circ\text{C}$	31
Drain Current-Pulsed ^{Note 1}	I_{DM}	126	A
Avalanche Current	I_{AR}	36	A
Single Pulse Avalanche Energy ^{Note 3}	E_{AS}	64	mJ
Maximum Power Dissipation	P_{tot}	9.6	W
Operating Junction Temperature Range	T_J	150	$^\circ\text{C}$

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Thermal resistance, Junction-to-Ambient ^{Note 2}	$R_{\theta JA}$	Steady State	-	50.9	-	$^\circ\text{C/W}$
Thermal resistance, Junction-to-Case	$R_{\theta JC}$	Steady State	-	13.0	-	$^\circ\text{C/W}$

Notes:

- Pulse Test: Pulse Width $\leq 10\text{ms}$, Duty Cycle $\leq 1\%$.
- For surface-mounted devices, both $R_{\theta JA}$ and $R_{\theta JC}$ are measured with the device mounted on approximately 1"×1" FR-4 PCBs. In actual applications, many factors including the PCB material and layout, may affect the thermal resistance of the device-board assembly. For best results, characterize the thermal resistance directly in the application circuit.
- Starting $T_J=25^\circ\text{C}$, $V_D=20\text{V}$, $L=0.1\text{mH}$, $V_{GS}=10\text{V}$.

Electrical Characteristics (T_J=25°C unless otherwise noted)

STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _{DS} =1mA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V, T _J =25°C	-	-	10	μA
		V _{DS} =24V, V _{GS} =0V, T _J =125°C	-	-	100	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

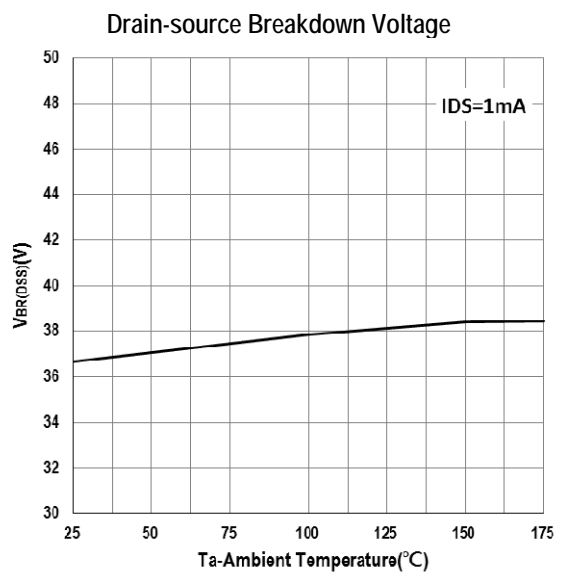
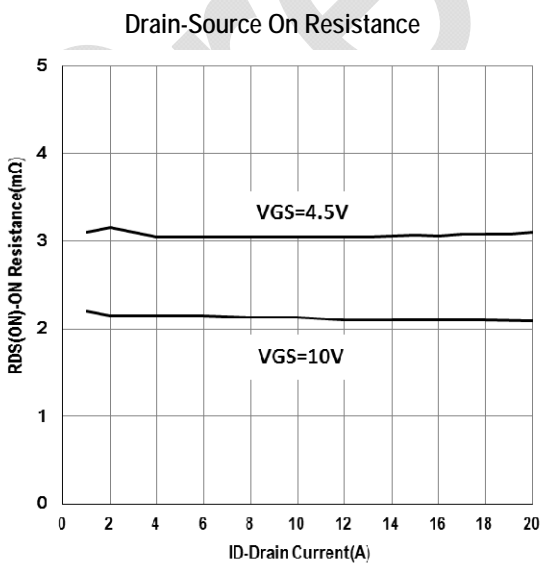
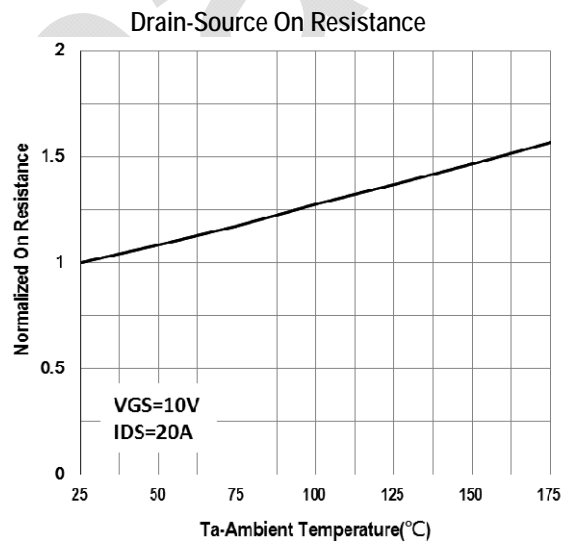
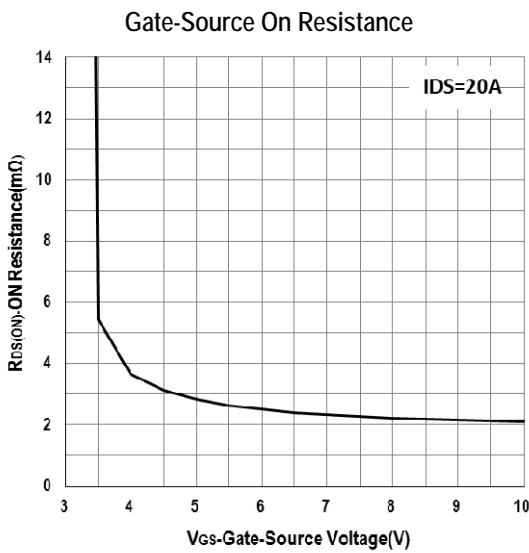
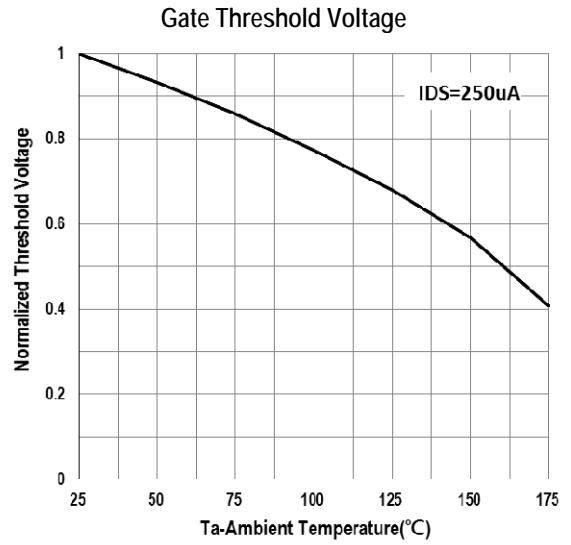
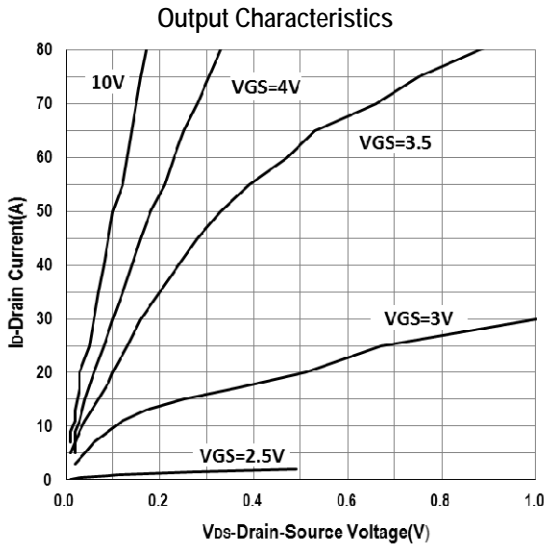
STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250μA	1.0	-	2.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =30A	-	-	2.7	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _{DS} =15A	-	-	4.2	mΩ
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	2.5	5.3	Ω
Forward Transconductance	g _{fs}	V _{DS} =5V, I _{DS} =20A	-	7.5	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	-	2273	-	pF
Output Capacitance	C _{oss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	-	1446	-	pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	-	106	-	pF
Turn-On Delay Time	T _{d(on)}	V _{DS} =15V, V _{GS} =10V, I _{DS} =20A, R _{GEN} =3Ω	-	10.6	-	ns
Rise Time	t _r	V _{DS} =15V, V _{GS} =10V, I _{DS} =20A, R _{GEN} =3Ω	-	57.3	-	ns
Turn-Off Delay Time	T _{d(off)}	V _{DS} =15V, V _{GS} =10V, I _{DS} =20A, R _{GEN} =3Ω	-	53.2	-	ns
Fall Time	t _f	V _{DS} =15V, V _{GS} =10V, I _{DS} =20A, R _{GEN} =3Ω	-	33.4	-	ns

GATE CHARGE CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate to Source Gate Charge	Q _{gs}	V _{DD} =15V, I _D =20A	-	7.84	-	nC
Gate charge at threshold	Q _{g(th)}	V _{DD} =15V, I _D =20A	-	3.77	-	nC
Gate to Drain Charge	Q _{gd}	V _{DD} =15V, I _D =20A	-	9.57	-	nC
Switching charge	Q _{sw}	V _{DD} =15V, I _D =20A	-	13.6	-	nC
Gate charge total	Q _g	V _{DD} =20V, I _D =20A, V _{GS} =0 to 10V	-	43.1	-	nC
Gate plateau voltage	V _{plateau}	V _{DD} =20V	-	3.23	-	V
Gate charge total, sync. FET (Q _g - Q _{gd})	Q _{g(sync)}		-	33.5	-	nC

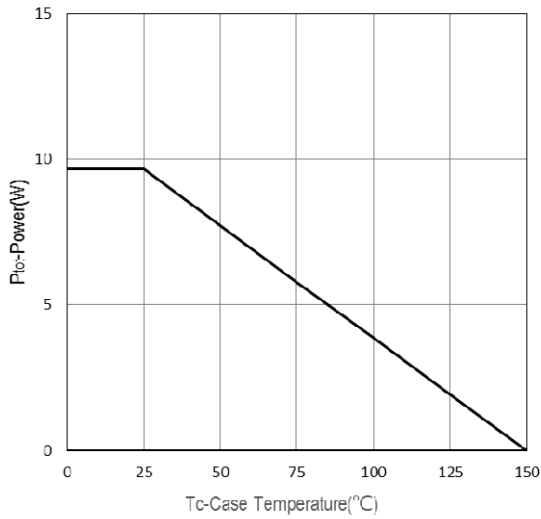
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _F =20A	-	0.7	1.3	V
Body Diode Reverse Recovery Time	t _{rr}	V _{DD} =24V, I _F =20A, di/dt=100A/μs	-	44.7	-	ns
		V _{DD} =24V, I _F =20A, di/dt=200A/μs	-	46.0	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}	V _{DD} =24V, I _F =20A, di/dt=100A/μs	-	41.4	-	nC
		V _{DD} =24V, I _F =20A, di/dt=200A/μs	-	66.1	-	nC
Reverse Recovery Current	I _{RRM}	V _{DD} =24V, I _F =20A, di/dt=100A/μs	-	1.61	-	A
		V _{DD} =24V, I _F =20A, di/dt=200A/μs	-	2.52	-	A

Typical Operating Characteristics

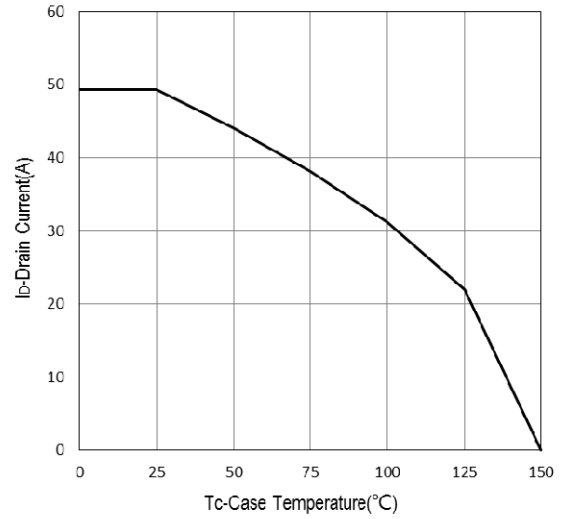


Typical Operating Characteristics (Cont.)

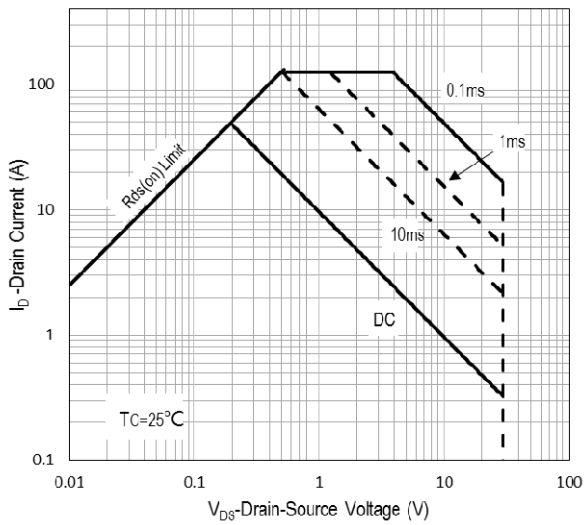
Power Dissipation



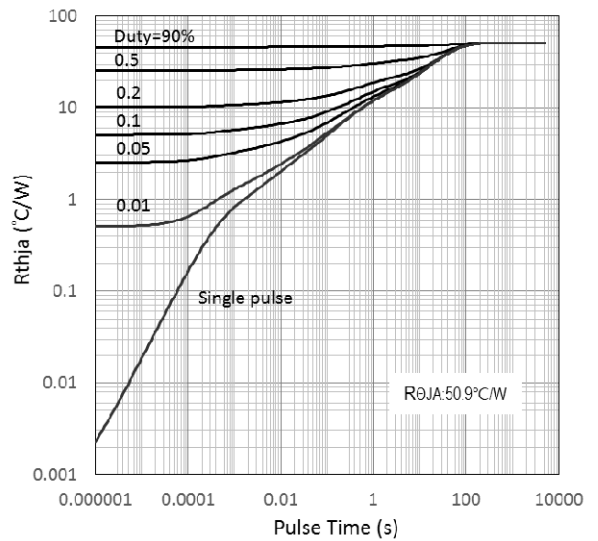
Drain Current



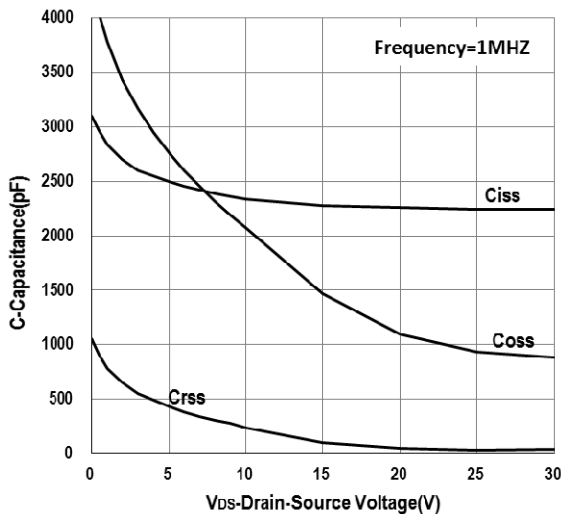
Safe Operation Area



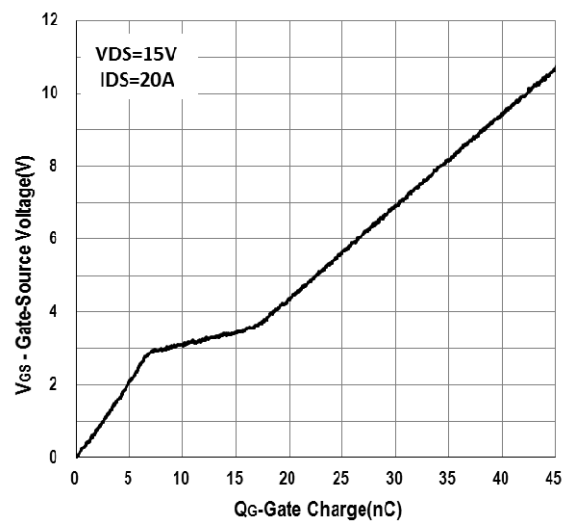
Transient Thermal Impedance



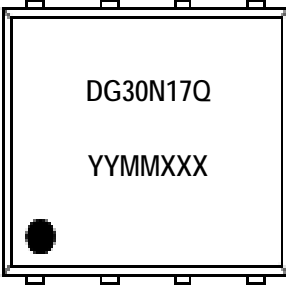
Capacitance



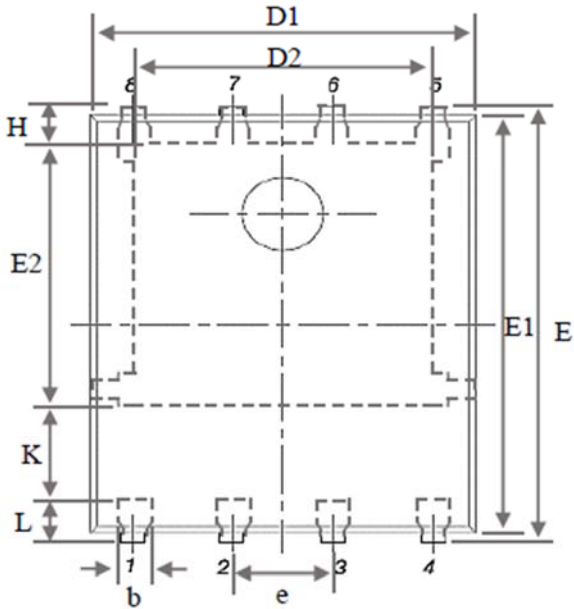
Gate Charge



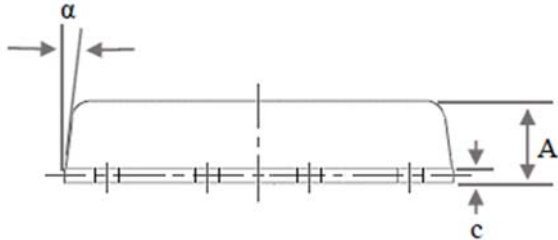
Marking Information

PDFN 5x6-8L (Q)	Marking Rule
<p>Laser Marking</p> 	<p><u>Line 1</u> : Device DG30N17Q</p> <p><u>Line 2</u> : Date Code YYMMXXX</p> <p>YY : Year Code MM : Month Code XXX : Serial Number</p>

Package of Dimension

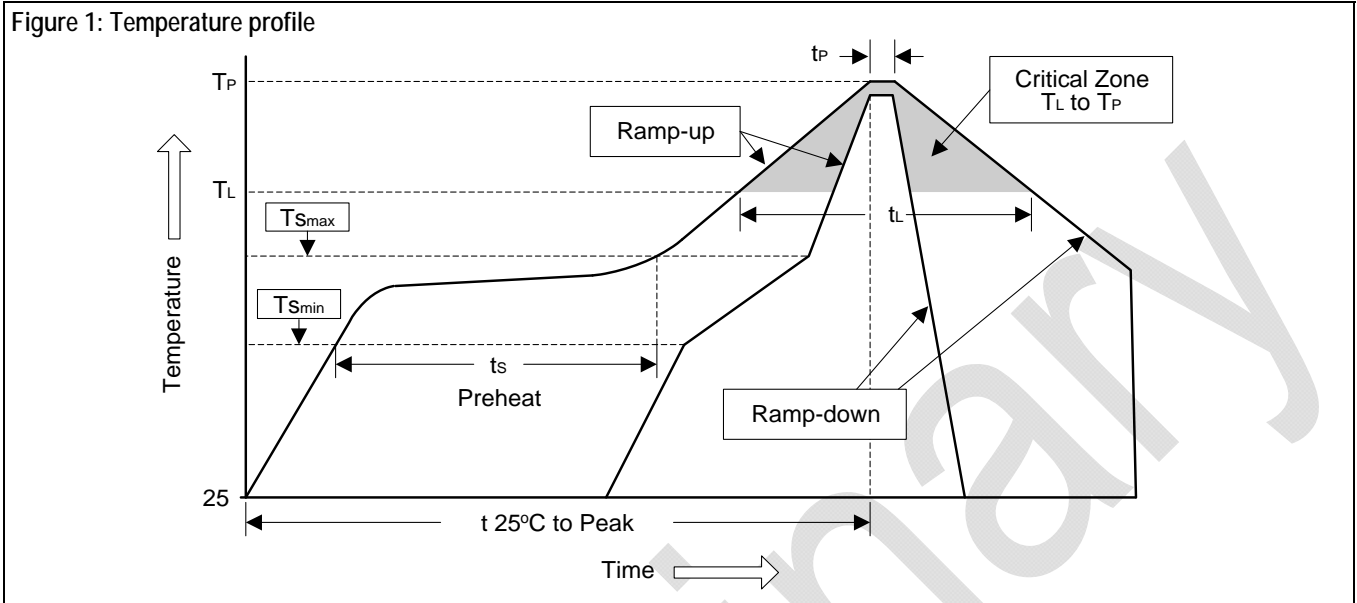


Symbol	Min	Nor	Max
A	0.90	1.04	1.17
b	0.33	0.42	0.51
C	0.06	0.20	0.35
D1	4.80	5.10	5.40
D2	3.61	3.96	4.31
E	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
e	1.27 BSC		
H	0.38	0.50	0.61
L	0.38	0.55	0.71
L1	0.05	0.15	0.25



Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60 to 120 sec	60 to 180 sec
T_{Smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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